

# PBSS4130T,215 Datasheet



DiGi Electronics Part Number	PBSS4
Manufacturer	Nexpe
Manufacturer Product Number	PBSS4
Description	TRANS
Detailed Description	Bipola W Surf

PBSS4130T,215-DG

Nexperia USA Inc.

PBSS4130T,215

TRANS NPN 30V 1A TO236AB

Bipolar (BJT) Transistor NPN 30 V 1 A 100MHz 480 m W Surface Mount TO-236AB

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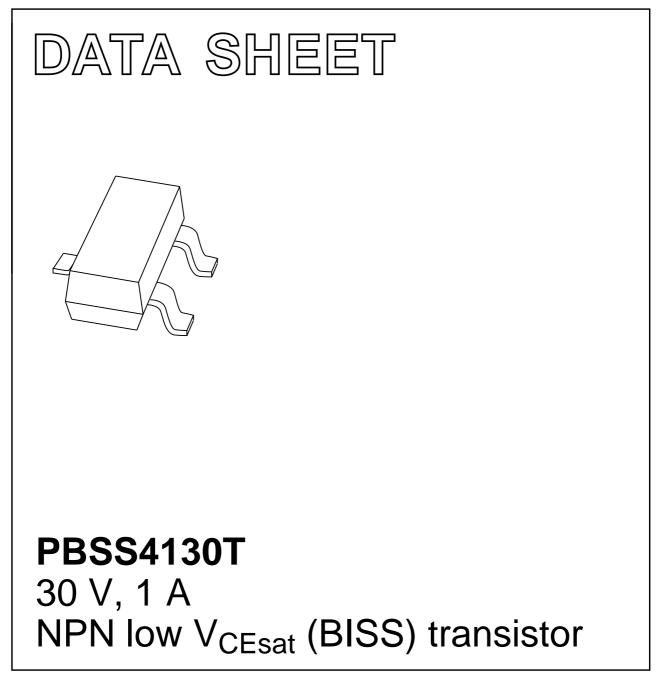
## Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
PBSS4130T,215	Nexperia USA Inc.
Series:	Product Status:
	Active
Transistor Type:	Current - Collector (Ic) (Max):
NPN	1 A
Voltage - Collector Emitter Breakdown (Max):	Vce Saturation (Max) @ lb, lc:
30 V	270mV @ 50mA, 1A
Current - Collector Cutoff (Max):	DC Current Gain (hFE) (Min) @ lc, Vce:
100nA (ICBO)	300 @ 500mA, 2V
Power - Max:	Frequency - Transition:
480 mW	100MHz
Operating Temperature:	Grade:
150°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q100	Surface Mount
Package / Case:	Supplier Device Package:
TO-236-3, SC-59, SOT-23-3	ТО-236АВ
Base Product Number:	
PBSS4130	

## **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.21.0075	

DISCRETE SEMICONDUCTORS



Product specification

2003 Nov 27



#### Philips Semiconductors

### 30 V, 1 A NPN low V<sub>CEsat</sub> (BISS) transistor

#### FEATURES

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability  $I_C$  and  $I_{CM}$
- High efficiency leading to less heat generation
- Reduced printed-circuit board requirements
- Cost effective alternative to MOSFETs in specific applications.

#### **APPLICATIONS**

- · Power management
  - DC/DC conversion
  - Supply line switching
  - Battery charger
  - LCD backlighting.
- Peripheral driver
  - Driver in low supply voltage applications (e.g. lamps and LEDs)
  - Inductive load drivers (e.g. relays, buzzers and motors).

#### DESCRIPTION

NPN BISS transistor in a SOT23 plastic package providing ultra low  $V_{CEsat}$  and  $R_{CEsat}$  parameters. PNP complement: PBSS5130T.

#### MARKING

TYPE NUMBER	MARKING CODE <sup>(1)</sup>
PBSS4130T	*3C

#### Note

1. \* = p: made in Hong Kong.

- \* = t: made in Malaysia.
  - \* = W: made in China.

#### **ORDERING INFORMATION**

#### QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V <sub>CEO</sub>	collector-emitter voltage	30	V
I <sub>C</sub>	collector current (DC)	1	А
I <sub>CM</sub>	peak collector current	3	А
R <sub>CEsat</sub>	equivalent on-resistance	220	mΩ

#### PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	

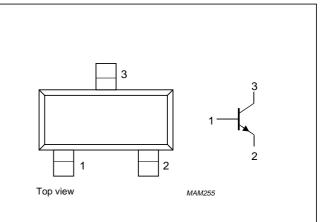


Fig.1 Simplified outline (SOT23) and symbol.

TYPE NUMBER		PACKAGE	
ITPE NUMBER	NAME	DESCRIPTION VERSI	
PBSS4130T	_	plastic surface mounted package; 3 leads	SOT23

### PBSS4130T

## 30 V, 1 A NPN low $V_{CEsat}$ (BISS) transistor

### PBSS4130T

#### LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>CBO</sub>	collector-base voltage	open emitter	_	40	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	30	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	5	V
I <sub>C</sub>	collector current (DC)		-	1	A
I <sub>CM</sub>	peak collector current		_	3	A
I <sub>BM</sub>	peak base current		_	300	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C; \text{ note } 1$	-	300	mW
		$T_{amb} \le 25 \ ^{\circ}C$ ; note 2	-	480	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C

#### Notes

- 1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
- 2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-a</sub>	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

#### Notes

- 1. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, standard footprint.
- 2. Device mounted on a FR4 printed-circuit board, single-sided copper, tinplated, mounting pad for collector 1 cm<sup>2</sup>.

## 30 V, 1 A NPN low $V_{CEsat}$ (BISS) transistor

### PBSS4130T

#### CHARACTERISTICS

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I <sub>CBO</sub>	collector-base cut-off current	$V_{CB} = 30 \text{ V}; \text{ I}_{E} = 0$	-	-	100	nA
		V <sub>CB</sub> = 30 V; I <sub>E</sub> = 0; T <sub>j</sub> = 150 °C	_	-	50	μA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 4 \text{ V}; \text{ I}_{C} = 0$	-	-	100	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 100 mA	350	470	-	
		$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 500 \text{ mA}$	300	450	-	
		$V_{CE} = 2 \text{ V}; \text{ I}_{C} = 1 \text{ A}$	300	420	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 1 mA	-	-	90	mV
		I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA	-	-	120	mV
		I <sub>C</sub> = 750 mA; I <sub>B</sub> = 15 mA	-	-	220	mV
		I <sub>C</sub> = 1 A; I <sub>B</sub> = 50 mA; note 1	-	-	270	mV
R <sub>CEsat</sub>	equivalent on-resistance	I <sub>C</sub> = 500 mA; I <sub>B</sub> = 50 mA; note 1	-	-	240	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	I <sub>C</sub> = 1 A; I <sub>B</sub> = 100 mA; note 1	-	-	1.1	V
V <sub>BEon</sub>	base-emitter turn-on voltage	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 100 mA	-	-	0.75	V
f <sub>T</sub>	transition frequency	I <sub>C</sub> = 100 mA; V <sub>CE</sub> = 10 V; f = 100 MHz	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; \text{ I}_{E} = \text{ I}_{e} = 0; \text{ f} = 1 \text{ MHz}$	-	-	20	pF

#### Note

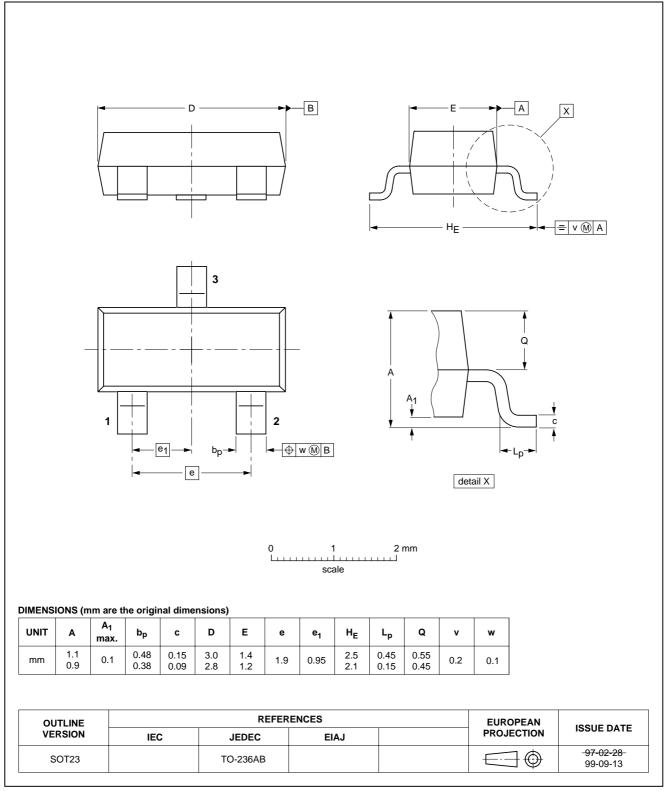
1. Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ .

PBSS4130T

## 30 V, 1 A NPN low $V_{CEsat}$ (BISS) transistor

#### PACKAGE OUTLINE





SOT23

## 30 V, 1 A NPN low $V_{CEsat}$ (BISS) transistor

PBSS4130T

#### DATA SHEET STATUS

LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)(3)</sup>	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
11	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
	Product data	Production	This data sheet contains data from the product specification. Philips Semiconductors reserves the right to make changes at any time in order to improve the design, manufacturing and supply. Relevant changes will be communicated via a Customer Product/Process Change Notification (CPCN).

#### Notes

- 1. Please consult the most recently issued data sheet before initiating or completing a design.
- 2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL http://www.semiconductors.philips.com.
- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

#### DEFINITIONS

**Short-form specification** — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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